

#### N-CHANNEL ENHANCEMENT MODE MOSFET

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C	
60V	3Ω @ V <sub>GS</sub> = 10V	SOT23	310mA	
60 V	4Ω @ V <sub>GS</sub> = 5V	30123	270mA	

## **Description**

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc





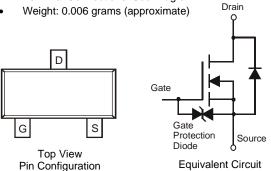
Top View

## **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 (3)
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram



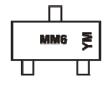
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8L-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



MM6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Kev

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	E	3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	310 240	mA		
Continuous Drain Current (Note 6) $V_{GS} = 5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	270 210	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	800	mA		
Maximum Body Diode Continuous Current (Note 5)	I <sub>S</sub>	500	mA		

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Dawer Dissination	(Note 6)	0	370	mW	
Total Power Dissipation	(Note 5)	P <sub>D</sub>	540		
Thermal Desigtance, Junction to Ambient	(Note 6)	0	348		
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ hetaJA}$	241	°C/W	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	91		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

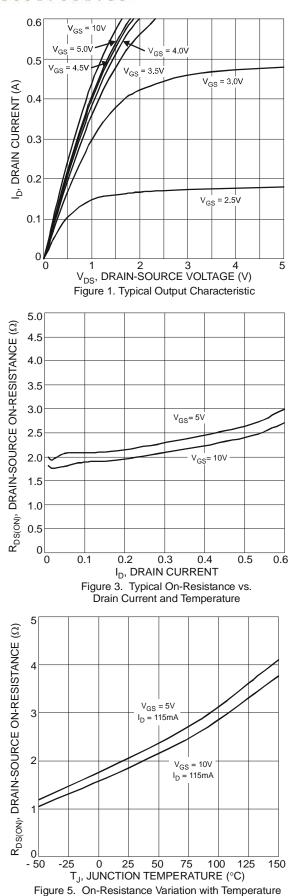
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	- Cymber		. , , ,	max	, <b>O</b>	1001 Containen	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±5	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	ē.	a.	a.	a.	a.		
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.2	_	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	2	3	Ω	$V_{GS} = 10V, I_D = 0.115A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	2.5	4	Ω	$V_{GS} = 5V, I_D = 0.115A$	
Forward Transconductance	g <sub>FS</sub>	80	290	_	mS	$V_{DS} = 10V, I_D = 0.115A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	22.0	_			
Output Capacitance	Coss	_	3.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.0	_			
Gate Resistance	R <sub>G</sub>	_	79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge V <sub>GS</sub> = 10V	Qg	_	0.87	_			
Total Gate Charge V <sub>GS</sub> = 4.5V	Qq	_	0.43	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$	
Gate-Source Charge	Q <sub>gs</sub>	_	0.11	_	nC	I <sub>D</sub> = 150mA	
Gate-Drain Charge	Q <sub>qd</sub>	_	0.11	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.7	_			
Turn-On Rise Time	t <sub>r</sub>	_	2.8	_	nS	$V_{DD} = 30V$ , $I_D = 0.115A$ , $V_{GEN} = 10V$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	12.6	_	n5	$R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	7.3	_			

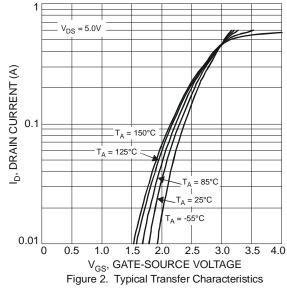
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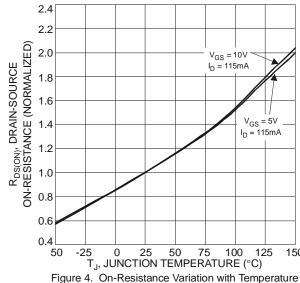
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7 .Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing

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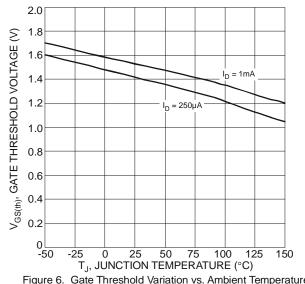
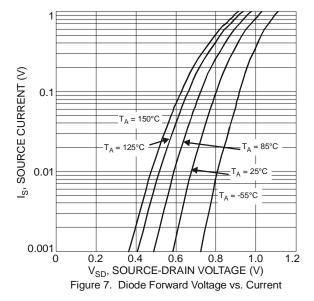


Figure 6. Gate Threshold Variation vs. Ambient Temperature





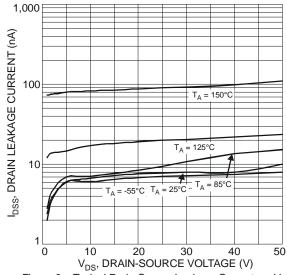
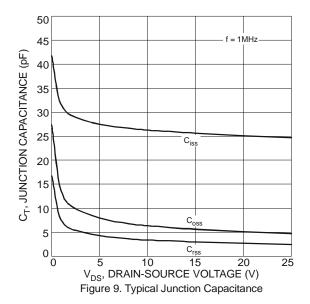
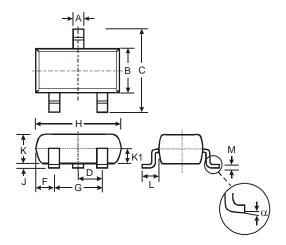


Figure 8. Typical Drain-Source Leakage Current vs. Voltage



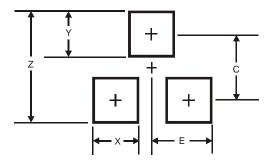


# **Package Outline Dimensions**



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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